

Chip Termination 250 Watts, 50Ω



Features:

- RoHS Compliant
- 250 Watts
- DC 2.2 GHz
- AIN Ceramic
- Non-Nichrome Resistive
 Element
- Low VSWR
- 100% Tested

Description

The A250N50X4 is high performance Aluminum Nitride (AIN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications

Resistive Element	Thick film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-50 to +200°C (see de rating chart)
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Tolerance is $\pm 0.010"$, unless otherwise specified. Designed to meet of exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications

Resistance Value:	50 Ohms, ± 2%
Power:	250 Watts
Frequency Range:	DC – 2.2 GHz
Return Loss	> 20 dB DC – 2.2 GHz
Creatification based on unit property installed using suggested mounting instructions	

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**





Model A250N50X4



Typical Performance:





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Mounting Footprint and Procedure:



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